NEW ENGLAND SEMICONDUCTOR

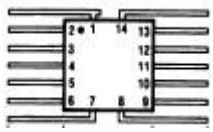
TECHNICAL DATA

NFQ3467
NFQ3468

1.0 AMPERE

40 - 50 VOLTS

0.5 WATTS



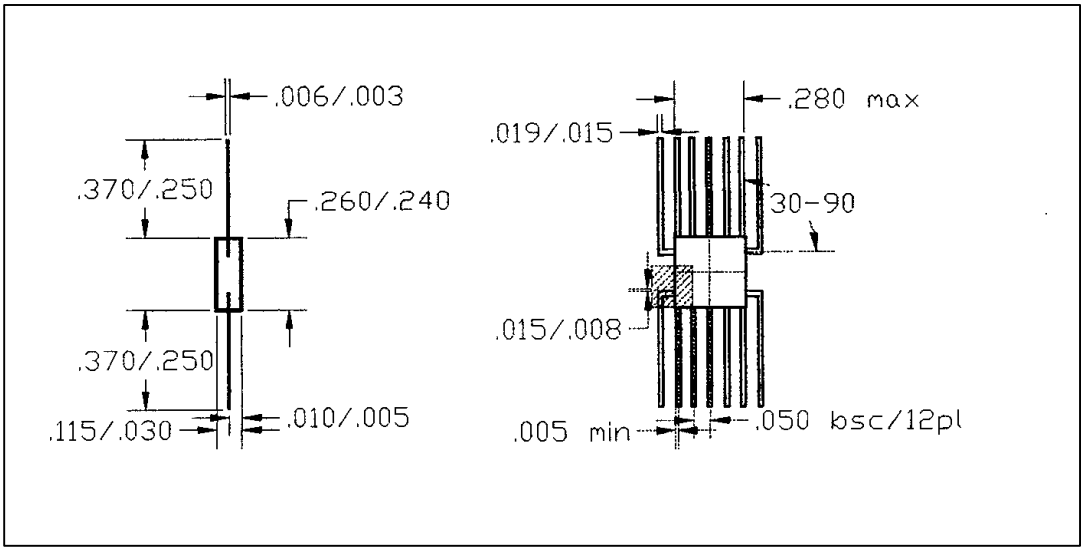
14 PIN
FLATPACK

QUAD MEMORY DRIVER
PNP TRANSISTOR

- LOW SATURATION VOLTAGE
- HIGH FREQUENCY

MAXIMUM RATINGS*

RATINGS	SYMBOL	NFQ3467	NFQ3468	UNITS
Collector-Emitter Voltage	V_{CEO}	40	50	Vdc
Collector-Base Voltage	V_{CBO}	40	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current -- Continuous	I_C	1.0		Adc
Total Power Dissipation @ $T_C = 25^0C$	P_D	0.5		W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		^0C



ELECTRICAL CHARACTERISTICS ($T_C = 25^0C$ unless otherwise noted)

Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (1) I_C = 10 mAdc, I_B = 0	$V_{CEO(sus)}$	40		Vdc
Emitter –Base Breakdown I_E = 10 mAdc, I_B = 0	V_{EBO}	5.0		Vdc
Collector-Emitter Cutoff Current V_{CE} = 30 Vdc, I_B = 0	I_{CBO}		200	ηAdc
Emitter-Base Cutoff Current V_{EB} = 3.0 Vdc, I_C = 0	I_{EBO}		200	ηAdc
ON CHARACTERISTICS (1)				
DC Current Gain I_C = 500 mAdc, V_{CE} = 1.0 Vdc	h_{FE}	20		
Collector-Emitter Saturation Voltage I_C =500 mAdc, I_b = 50 mAdc	$V_{CE(sat)}$		0.5	Vdc
Base-Emitter Saturation Voltage I_C =500 mAdc, I_b = 50 mAdc	$V_{BE(sat)}$		1.2	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain -- Bandwidth Product I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz	f_T	125		MHz
Output Capacitance V_{CB} = 10 Vdc, I_E = 0	C_{obo}		25	pF
SWITCHING CHARACTERISTICS				
Turn-On Time I_C = 500 mAdc; I_{B1}= 50 mAdc	t_{on}		40	ηs
Turn-Off Time I_C = 500 mAdc; I_{B1} = -I_{B2} = 50 mAdc	t_{off}		90	ηs

(1)Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.